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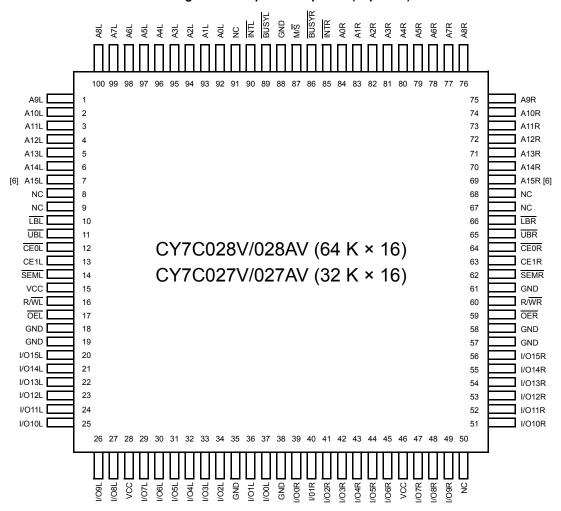
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Pin Configurations

Figure 1. 100-pin TQFP pinout (Top View)



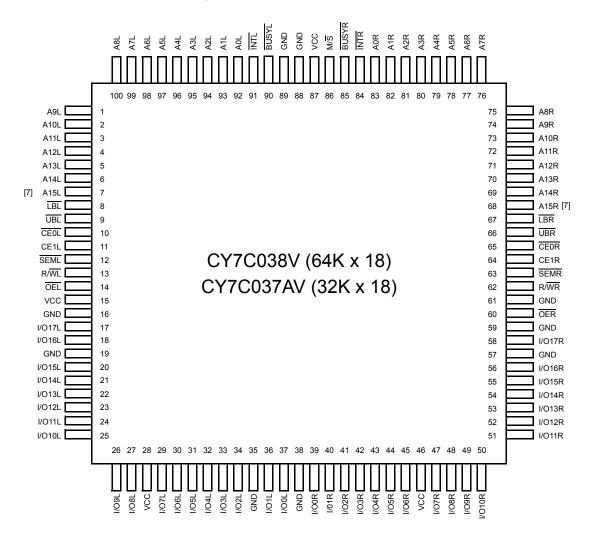
Note

6. This pin is NC for CY7C027V/027AV.



Pin Configurations(continued)

Figure 2. 100-pin TQFP pinout (Top View)



Note

7. This pin is NC for CY7C037AV.



Selection Guide

Parameter	-15	-20	-25	Unit
Maximum access time	15	20	25	ns
Typical operating current	125	120	115	mA
Typical standby current for I _{SB1} (Both ports TTL level)	35	35	30	mA
Typical standby current for I _{SB3} (Both ports CMOS level)	10	10	10	μΑ

Pin Definitions

Left Port	Right Port	Description
CE _{0L} , CE _{1L}	CE _{0R} , CE _{1R}	Chip Enable (\overline{CE} is LOW when $\overline{CE}_0 \le V_{IL}$ and $CE_1 \ge V_{IH}$)
R/W _L	R/W _R	Read/Write Enable
OE _L	0E _R	Output Enable
A _{0L} –A _{15L}	A _{0R} -A _{15R}	Address (A ₀ –A ₁₄ for 32K; A ₀ –A ₁₅ for 64K devices)
I/O _{0L} –I/O _{17L}	I/O _{0R} –I/O _{17R}	Data bus input/output (I/O ₀ –I/O ₁₅ for × 16 devices; I/O ₀ –I/O ₁₇ for × 18)
SEM _L	SEMR	Semaphore Enable
UB _L	UB _R	Upper byte select (I/O ₈ –I/O ₁₅ for × 16 devices; I/O ₉ –I/O ₁₇ for × 18 devices)
LB _L	LB _R	Lower byte select (I/O ₀ –I/O ₇ for × 16 devices; I/O ₀ –I/O ₈ for × 18 devices)
INT _L	INT _R	Interrupt flag
BUSY _L	BUSYR	Busy flag
M/S		Master or Slave select
V _{CC}		Power
GND		Ground
NC		No connect

Architecture

The CY7C027V/027AV/028V/028AV and CY7037AV/038V consist of an array of 32K and 64K words of 16 and 18 bits each of dual-port RAM cells, I/O and address lines, and control signals (CE, OE, RW). These control pins permit independent access for reads or writes to any location in memory. To handle simultaneous writes/reads to the same location, a BUSY pin is provided on each port. Two interrupt (INT) pins can be utilized for port-to-port communication. Two semaphore (SEM) control pins are used for allocating shared resources. With the M/S pin, the devices can function as a master (BUSY pins are outputs) or as a slave (BUSY pins are inputs). The devices also have an automatic power down feature controlled by CE. Each port is provided with its own output enable control (OE), which allows data to be read from the device.

Functional Description

The CY7C027V/027AV/028V/028AV and CY7037AV/038V are low power CMOS 32K, 64K x 16/18 dual-port static RAMs. Various arbitration schemes are included on the devices to handle situations when multiple processors access the same piece of data. Two ports are provided, permitting independent, asynchronous access for reads and writes to any location in memory. The devices can be utilized as stand-alone 16/18-bit dual-port static RAMs or multiple devices can be combined to

function as <u>a</u> 32/36-bit or wider master/slave dual-port static RAM. An M/S pin is provided for implementing 32/36-bit or wider memory applications without the need for separate master and slave devices or additional discrete logic. Application areas include interprocessor/multiprocessor designs, communications status buffering, and dual-port video/graphics memory.

Each port has independent control pins: Chip Enable (\overline{CE}) , Read or Write Enable (R/W), and Output Enable (OE). Two flags are provided on each port (BUSY) and (INT). BUSY signals that the port is trying to access the same location currently being accessed by the other port. The interrupt flag (INT) permits communication between ports or systems by means of a mail box. The semaphores are used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphore logic is comprised of eight shared latches. Only one side can control the latch (semaphore) at any time. Control of a semaphore indicates that a shared resource is in use. An automatic power down feature is controlled independently on each port by a chip select (\overline{CE}) pin.

The CY7C027V/027AV/028V/028AV and CY7037AV/038V are available in 100-pin Thin Quad Plastic Flatpacks (TQFP).

Write Operation

Data must be set up for a duration of t_{SD} before the rising edge of RW to guarantee a valid write. A write operation is controlled by either the RW pin (see Figure 7) or the CE pin (see Figure 8). Required inputs

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for non-contention operations are summarized in Non-Contending Read/Write on page 17.

If a location is being written to by one port and the opposite port attempts to read that location, a port-to-port flowthrough delay must occur before the data is read on the output; otherwise the data read is not deterministic. Data is valid on the port t_{DDD} after the data is presented on the other port.

Read Operation

When reading the device, the user must assert both the \overline{OE} and \overline{CE} pins. Data is available t_{ACE} after \overline{CE} or t_{DOE} after \overline{OE} is asserted. If the user wishes to access a semaphore flag, then the \overline{SEM} pin must be asserted instead of the \overline{CE} pin, and \overline{OE} must also be asserted.

Interrupts

The upper two memory locations may be used for message passing. The highest memory location (7FFF for the CY7C027V/037AV/027AV, FFFF for the CY7C028V/028AV/38V) is the mailbox for the right port and the second-highest memory location (7FFE for the CY7C027V/027AV/037AV, FFFE for the CY7C028V/028AV/38V) is the mailbox for the left port. When one port writes to the other port's mailbox, an interrupt is generated to the owner. The interrupt is reset when the owner reads the contents of the mailbox. The message is user defined.

Each port can read the other port's mailbox without resetting the interrupt. The active state of the busy signal (to a port) prevents the port from setting the interrupt to the winning port. Also, an active busy to a port prevents that port from reading its own mailbox and, thus, resetting the interrupt to it.

If an application does not require message passing, do not connect the interrupt pin to the processor's interrupt request input pin.

The operation of the interrupts and their interaction with Busy are summarized in Interrupt Operation Example on page 17.

Busy

The CY7C027V/027AV/028V/028AV and CY7037AV/038V provide on-chip arbitration to resolve simultaneous memory location access (contention). If both ports' $\overline{\text{CE}}$ s are asserted and an address match occurs within t_{PS} of each other, the busy logic determines which port has access. If t_{PS} is violated, one port definitely gains permission $t_{\overline{\text{O}}}$ the location, but it is not predictable which port gets that permission. BUSY is asserted t_{BLA} after an address match or t_{BLC} after $\overline{\text{CE}}$ is taken LOW.

Master/Slave

A M/S pin is provided to expand the word width by configuring the device as either a master or a slave. The BUSY output of the master is

connected to the $\overline{\text{BUSY}}$ input of the slave. This allows the device to interface to a master device with no external <u>comp</u>onents. Writing to slave devices must be delayed until after the $\overline{\text{BUSY}}$ input has settled (t_{BLC} or t_{BLA}), otherwise, the slave chip may begin a write cycle during a contention situation. When tied HIGH, $\underline{\text{the M/S}}$ pin allows the $\underline{\text{device}}$ to be used as a master and, therefore, the $\underline{\text{BUSY}}$ line is an output. $\underline{\text{BUSY}}$ can then be used to send the arbitration outcome to a slave.

Semaphore Operation

The CY7C027V/027AV/028V/028AV and CY7037AV/038V provide eight semaphore latches, which are separate from the dual-port memory locations. Semaphores are used to reserve resources that are shared between the two ports. The state of the semaphore indicates that a resource is in use. For example, if the left port wants to request a given resource, it sets a latch by writing a zero to a semaphore location. The left port then verifies its success in setting the latch by reading it. After writing to the semaphore, SEM or OE must be deasserted for t_{SOP} before attempting to read the semaphore. The semaphore value is available t_{SWRD} + t_{DOE} after the rising edge of the semaphore write. If the left port was successful (reads a zero), it assumes control of the shared resource, otherwise (reads a one) it assumes the right port has control and continues to poll the semaphore. When the right side has relinquished control of the semaphore (by writing a one), the left side succeeds in gaining control of the semaphore. If the left side no longer requires the semaphore, a one is written to cancel its request.

Semaphores are accessed by asserting $\overline{\text{SEM}}$ LOW. The $\overline{\text{SEM}}$ pin functions as <u>a chip</u> select for the semaphore latches ($\overline{\text{CE}}$ must remain HIGH <u>during SEM LOW</u>). A₀₋₂ represents the semaphore address. $\overline{\text{OE}}$ and R/W are used in the same manner as a normal memory access. When writing or reading a semaphore, the other address pins have no effect

When writing to the semaphore, only I/O_0 is used. If a zero is written to the left port of an available semaphore, a one appears at the same semaphore address on the right port. That semaphore can now only be modified by the side showing zero (the left port in this case). If the left port now relinquishes control by writing a one to the semaphore, the semaphore is set to one for both sides. However, if the right port had requested the semaphore (written a zero) while the left port had control, the right port would immediately own the semaphore as soon as the left port released it. Semaphore Operation Example on page 18 shows sample semaphore operations.

When reading a semaphore, all sixteen/eighteen data lines output the semaphore value. The read value is latched in an output register to prevent the semaphore from changing state during a write from the other port. If both ports attempt to access the semaphore within t_{SPS} of each other, the semaphore is definitely obtained by one side or the other, but there is no guarantee which side controls the semaphore.

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Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested. Storage temperature-65 °C to +150 °C Ambient temperature with power applied55 °C to +125 °C Supply voltage to ground potential-0.5 V to +4.6 V

outputs in High Z state-0.5 V to V_{CC} + 0.5 V

DC input voltage $^{[8]}$ –0.5 V to V $_{CC}$ + 0.5 V Static discharge voltage > 1100 V Latch-up current > 200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0 °C to +70 °C	$3.3~V\pm300~mV$
Industrial [9]	–40 °C to +85 °C	$3.3~V\pm300~mV$

Electrical Characteristics

Over the Operating Range

DC voltage applied to

	CY7C027V/027AV/028V/028AV/CY7C037AV/CY7C038V											
Parameter	Description	Description -15								-25		
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
V _{OH}	Output HIGH voltage (V_{CC} = Min., I_{CC}	2.4	_		2.4	_	_	2.4	_	_	V	
V_{OL}	Output LOW voltage (V_{CC} = Min., I_{C}	_{oH} = +4.0 mA)	-		0.4	_		0.4	_		0.4	V
V_{IH}	Input HIGH voltage		2.2		_	2.2		_	2.2		_	V
V_{IL}	Input LOW voltage		-		0.8	_		0.8	_		0.8	V
I _{IX}	Input leakage current		-5		5	-5		5	-5		5	μА
I _{OZ}	Output leakage current		-10		10	-10		10	-10		10	μА
I _{CC}	Operating current	Commercial	_	125	185	_	120	175	_	115	165	mA
	(V _{CC} = Max., I _{OUT} = 0 mA) outputs disabled	Industrial ^[9]		-	_		140	195		-	-	mA
I _{SB1}	Standby current	Commercial		35	50		35	45		30	40	mA
	(Both ports TTL level) $CE_L \& CE_R \ge V_{IH}, f = f_{MAX}$	Industrial ^[9]		-	_		45	55		-	_	mA
I _{SB2}	Standby current	Commercial		80	120		75	110		65	95	mA
	(One port TTL level) $CE_L \mid CE_R \ge V_{IH}$, $f = f_{MAX}$	Industrial ^[9]		-	-		85	120		-	-	mA
I _{SB3}	Standby current	Commercial		10	250		10	250		10	250	μА
	(Both ports CMOS level) $CE_L \& CE_R \ge V_{CC} - 0.2 \text{ V, f = 0}$	Industrial ^[9]		-	_		10	250		-	_	μА
I _{SB4}	Standby current	Commercial		75	105		70	95		60	80	mA
	$\frac{\text{(One port CMOS level)}}{\text{CE}_{L} \mid \text{CE}_{R} \ge \text{V}_{\text{IH}}, \text{f = f}_{\text{MAX}}^{[10]}$	Industrial ^[9]		-	-		80	105		-	-	mA

Capacitance

Parameter [11]	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = 3.3 \text{V}$	10	pF
C _{OUT}	Output capacitance		10	pF

- 8. Pulse width < 20 ns.
- 9. Industrial parts are available in CY7C028V and CY7C038V, CY7C027V/027AV only.
- 10. f_{MAX} = 1/t_{RC} = All inputs cycling at f = 1/t_{RC} (except output enable), f = 0 means no address or control lines change. This applies only to inputs at CMOS level standby I_{SB3}.

 11. Tested initially and after any design or process changes that may affect these parameters.

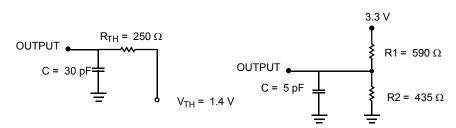
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AC Test Loads and Waveforms

OUTPUT C = 30 pF $R1 = 590 \Omega$ $R2 = 435 \Omega$

Figure 3. AC Test Loads and Waveforms

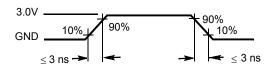


(a) Normal Load (Load 1)

(b) Thévenin Equivalent (Load 1)

ALL INPUTPULSES

(c) Three-State Delay (Load 2) (Used for t_{LZ}, t_{HZ}, t_{HZWE}, & t_{LZWE} including scope and jig)

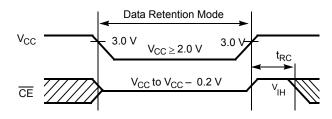


Data Retention Mode

The CY7C027V/027AV/028V/028AV and CY7037AV/038V are designed with battery backup in mind. Data retention voltage and supply current are guaranteed over temperature. The following rules ensure data retention:

- 1. Chip Enable ($\overline{\text{CE}}$) must be held HIGH during data retention, within V_{CC} to V_{CC} 0.2 V
- 2. $\overline{\text{CE}}$ must be kept between V_{CC} 0.2 V and 70% of V_{CC} during the power up and power down transitions
- 3. The RAM can begin operation >t $_{RC}$ after V_{CC} reaches the minimum operating voltage (3.0 V)

Timing



Parameter	Test Conditions [12]	Max	Unit
ICC _{DR1}	At VCC _{DR} = 2 V	50	μΑ

Note

12. $\overline{\text{CE}}$ = V_{CC}, V_{in} = GND to V_{CC}, T_A = 25° C. This parameter is guaranteed but not tested.

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Switching Characteristics

Over the Operating Range

_ [12]			СҮ		AV/028V/028 V/CY7C038V			
Parameter [13]	Description	-	15		20		25	Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle								
t _{RC}	Read cycle time	15	-	20	-	25	_	ns
t _{AA}	Address to data valid	_	15	_	20	_	25	ns
t _{OHA}	Output hold from address change	3	_	3	_	3	_	ns
t _{ACE} ^[14]	CE LOW to data valid	-	15	-	20	-	25	ns
t _{DOE}	OE LOW to data valid	-	10	-	12	-	13	ns
t _{LZOE} [15, 16, 17]	OE LOW to Low Z	3	_	3	_	3	_	ns
t _{HZOE} [15, 16, 17]	OE HIGH to High Z	-	10	_	12	-	15	ns
t _{LZCE} [15, 16, 17]	CE LOW to Low Z	3	_	3	_	3	_	ns
t _{HZCE} ^[15, 16, 17]	CE HIGH to High Z	-	10	_	12	-	15	ns
t _{PU} ^[17]	CE LOW to power-up	0	_	0	_	0	_	ns
t _{PD} ^[17]	CE HIGH to power-down	-	15	-	20	-	25	ns
t _{ABE} ^[14]	Byte enable access time	-	15	_	20	-	25	ns
Write Cycle			•		•	•		•
t _{WC}	Write cycle time	15	-	20	_	25	_	ns
t _{SCE} ^[14]	CE LOW to write end	12	-	16	-	20	_	ns
t _{AW}	Address valid to write end	12	-	16	_	20	_	ns
t _{HA}	Address hold from write end	0	_	0	-	0	_	ns
t _{SA} ^[14]	Address setup to write start	0	-	0	-	0	_	ns
t _{PWE}	Write pulse width	12	_	17	_	22	_	ns
t _{SD}	Data setup to write end	10	_	12	_	15	_	ns
t _{HD}	Data hold from write end	0	-	0	_	0	_	ns
t _{HZWE} [16, 17]	R/W LOW to High Z	_	10	_	12	_	15	ns
t _{LZWE} [16, 17]	R/W HIGH to Low Z	3	-	3	-	3	_	ns
t _{WDD} ^[18]	Write pulse to data delay	-	30	_	40	-	50	ns
t _{DDD} ^[18]	Write data valid to read data valid	-	25	_	30	_	35	ns

^{13.} Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_Q/I_{QH} and 30 pF load capacitance.

14. To access RAM, CE=L, UB=L, SEM=H. To access semaphore, CE=H and SEM=L. Either condition must be valid for the entire t_{SCE} time.

15. At any given temperature and voltage condition for any given device, t_{HZCE} is less than t_{LZCE} and t_{HZOE} is less than t_{LZCE}.

16. Test conditions used are Load 2.

 ^{17.} This parameter is guaranteed by design, but it is not production tested. For information on port-to-port delay through RAM cells from writing port to reading port, refer to Figure 11.
 18. t_{BDD} is a calculated parameter and is the greater of t_{WDD}-t_{PWE} (actual) or t_{DDD}-t_{SD} (actual).



Switching Characteristics(continued)

Over the Operating Range

[13]		CY7C027V/027AV/028V/028AV/ CY7C037AV/CY7C038V									
Parameter [13]	Description	-	15	-:	20	-2	Unit				
		Min	Max	Min	Max	Min	Max				
Busy Timing	[19]			•	•		•	•			
t _{BLA}	BUSY LOW from address match	_	15	_	20	_	20	ns			
t _{BHA}	BUSY HIGH from address mismatch	_	15	_	20	-	20	ns			
t _{BLC}	BUSY LOW from CE LOW	-	15	-	20	_	20	ns			
t _{BHC}	BUSY HIGH from CE HIGH	-	15	-	16	_	17	ns			
t _{PS}	Port setup for priority	5	-	5	-	5	-	ns			
t _{WB}	R/W HIGH after BUSY (Slave)	0	_	0	-	0	_	ns			
t _{WH}	R/W HIGH after BUSY HIGH (Slave)	13	_	15	-	17	_	ns			
t _{BDD} ^[20]	BUSY HIGH to data valid	-	15	-	20	_	25	ns			
Interrupt Tim	ning ^[19]			•	•		•	•			
t _{INS}	INT set time	_	15	_	20	_	20	ns			
t _{INR}	INT reset time	-	15	-	20	_	20	ns			
Semaphore ⁻	Timing			•	•		•	•			
t _{SOP}	SEM flag update pulse (OE or SEM)	10	_	10	_	12	_	ns			
t _{SWRD}	SEM flag write to read time	5	_	5	_	5	_	ns			
t _{SPS}	SEM flag contention window	5	_	5	-	5	-	ns			
t _{SAA}	SEM address access time	_	15	-	20	_	25	ns			

^{19.} For information on port-to-port delay through RAM cells from writing port to reading port, refer to Figure 11 waveform. 20. t_{BDD} is a calculated parameter and is the greater of t_{WDD}-t_{PWE} (actual) or t_{DDD}-t_{SD} (actual).



Switching Waveforms

Figure 4. Read Cycle No. 1 (Either Port Address Access) [21, 22, 23]

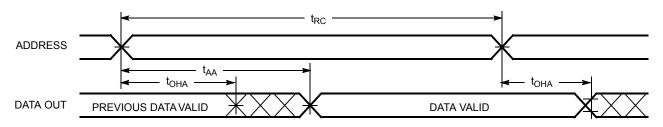


Figure 5. Read Cycle No. 2 (Either Port CE/OE Access) [21, 24, 25]

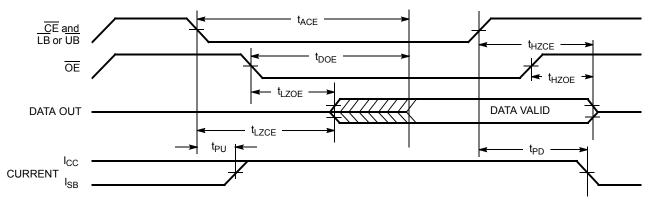
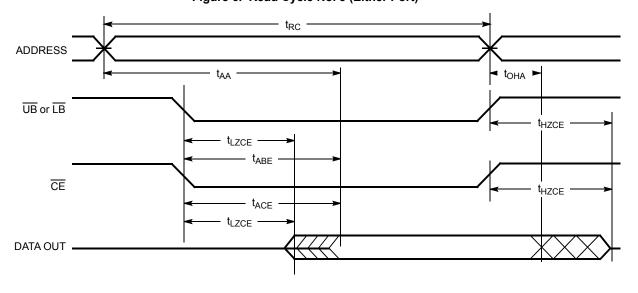


Figure 6. Read Cycle No. 3 (Either Port) $^{[21,\ 23,\ 24,\ 25]}$



Notes

- 21. R/\overline{W} is HIGH for read cycles.
- 22. Device is continuously selected $\overline{CE} = V_{IL}$ and \overline{UB} or $\overline{LB} = V_{IL}$. This waveform cannot be used for semaphore reads.

- 24. Address valid prior to or coincident with \overline{CE} transition LOW.

 25. To access RAM, $\overline{CE} = V_{\parallel L}$, \overline{UB} or $\overline{LB} = V_{\parallel L}$, $\overline{SEM} = V_{\parallel H}$. To access semaphore, $\overline{CE} = V_{\parallel H}$, $\overline{SEM} = V_{\parallel L}$.



Figure 7. Write Cycle No. 1: R/W Controlled Timing [26, 27, 28, 29]

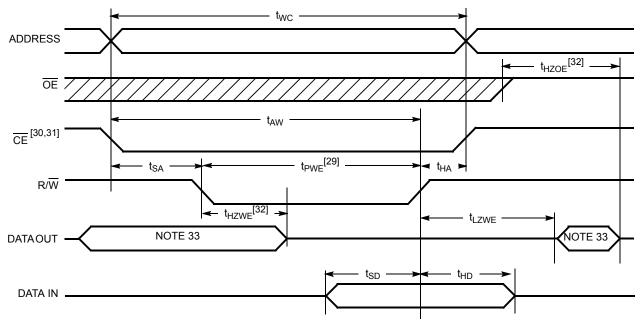
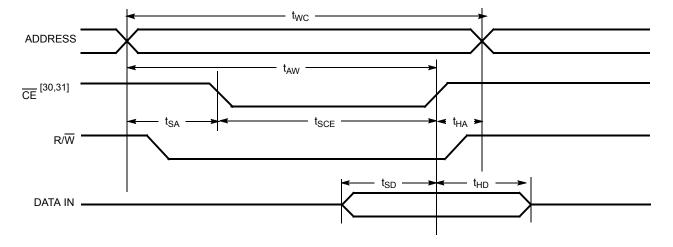


Figure 8. Write Cycle No. 2: CE Controlled Timing [26, 27, 28, 34]



- 26. R/W must be HIGH during all address transitions.

- 26. R/W must be HIGH during all address transitions.
 27. A write occurs during the overlap (t_{SCE} or t_{PWE}) of a LOW CE or SEM and a LOW UB or LB.
 28. t_{HA} is measured from the earlier of CE or R/W or (SEM or R/W) going HIGH at the end of write cycle.
 29. If OE is LOW during a R/W controlled write cycle, the write pulse width must be the larger of t_{PWE} or (t_{HZWE} + t_{SD}) to allow the I/O drivers to turn off and data to be placed on the bus for the required t_{SD}. If OE is HIGH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t_{PWE}.
 30. To access RAM, CE = V_{II}, SEM = V_{II}, SEM = V_{II}.
 31. To access upper byte, CE = V_{II}, LB = V_{II}, SEM = V_{II}.
 32. Transition is measured ±500 mV from steady state with a 5 pF load (including scope and jig). This parameter is sampled and not 100% tested.
 33. During this paried, the I/O pines are in the out with state, and input signals must not be applied.

- 33. During this period, the I/O pins are in the output state, and input signals must not be applied.

 34. If the CE or SEM LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the high impedance state.



Figure 9. Semaphore Read After Write Timing, Either Side [35]

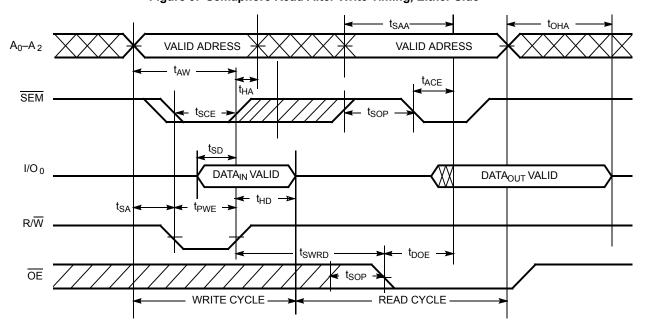
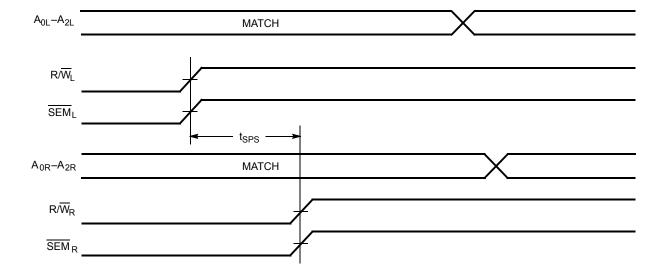


Figure 10. Timing Diagram of Semaphore Contention $^{[36,\ 37,\ 38]}$



- 35. $\overline{\text{CE}}$ = HIGH for the duration of the above timing (both write and read cycle). 36. I/O_{0R} = I/O_{0L} = LOW (request semaphore); $\overline{\text{CE}}_{R}$ = $\overline{\text{CE}}_{L}$ = HIGH. 37. Semaphores are reset (available to both ports) at cycle start.

- 38. If t_{SPS} is violated, the semaphore is definitely obtained by one side or the other, but which side gets the semaphore is unpredictable.



Figure 11. Timing Diagram of Read with BUSY (M/S = HIGH) [39]

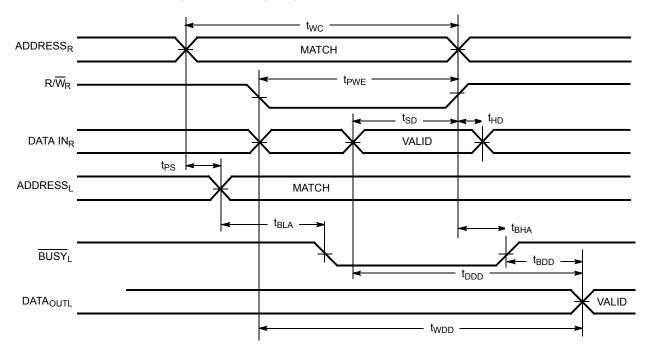
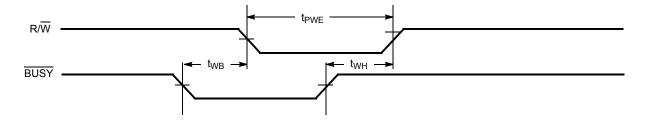


Figure 12. Write Timing with Busy Input ($M/\overline{S} = LOW$)



Note 39. $\overline{CE}_L = \overline{CE}_R = LOW$.



Figure 13. Busy Timing Diagram No. 1 ($\overline{\text{CE}}$ Arbitration) [40]

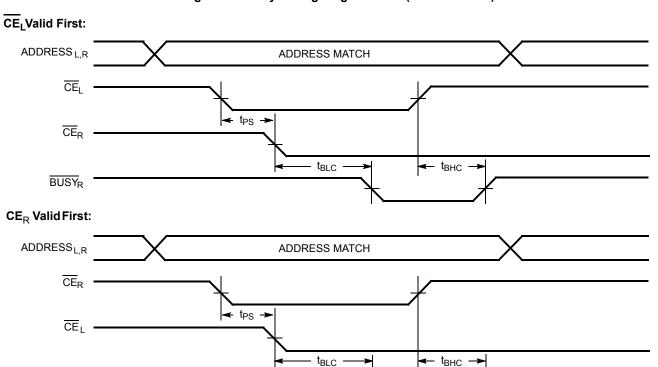
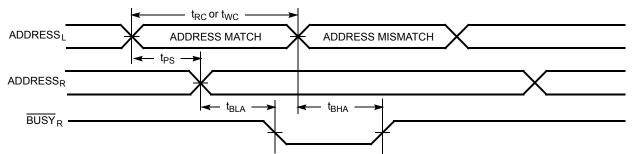


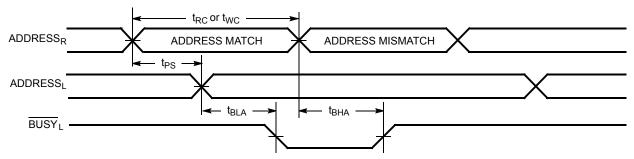
Figure 14. Busy Timing Diagram No. 2 (Address Arbitration) [40]

Left Address Valid First:

BUSYL



Right Address Valid First:



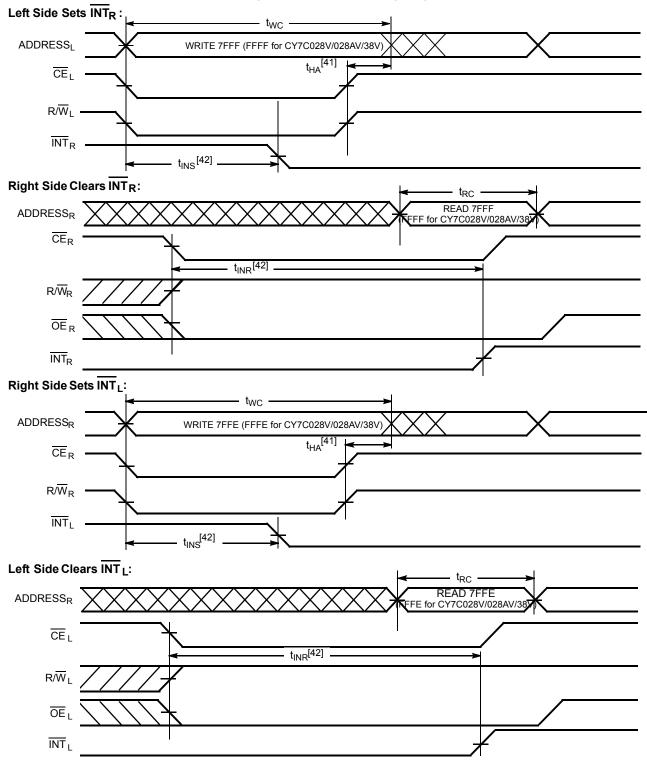
Note

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^{40.} If t_{PS} is violated, the busy signal is asserted on one side or the other, but there is no guarantee to which side $\overline{\text{BUSY}}$ is asserted.



Figure 15. Interrupt Timing Diagrams



Notes

- 41. t_{HA} depends on which enable pin $(\overline{CE}_L \text{ or } \overline{R/W}_L)$ is <u>deasserted first</u>.
 42. t_{INS} or t_{INR} depends on which enable pin $(\overline{CE}_L \text{ or } R/W_L)$ is asserted last.



Non-Contending Read/Write

		Inp	uts			Ou	itputs	
CE	R/W	OE	UB	LB	SEM	I/O ₉ -I/O ₁₇	I/O ₀ –I/O ₈	Operation
Н	Х	Х	Х	Х	Н	High Z	High Z	Deselected: Power-down
Х	Х	Х	Н	Н	Н	High Z	High Z	Deselected: Power-down
L	L	Х	L	Н	Н	Data in	High Z	Write to upper byte only
L	L	Х	Н	L	Н	High Z	Data in	Write to lower byte only
L	L	Х	L	L	Н	Data in	Data in	Write to both bytes
L	Н	L	L	Н	Н	Data out	High Z	Read upper byte only
L	Н	L	Н	L	Н	High Z	Data out	Read lower byte only
L	Н	L	L	L	Н	Data out	Data out	Read both bytes
Х	Х	Н	Х	Х	Х	High Z	High Z	Outputs disabled
Н	Н	L	Х	Х	L	Data out	Data out	Read data in semaphore flag
Х	Н	L	Н	Н	L	Data out	Data out	Read data in semaphore flag
Н		Х	Х	Х	L	Data in	Data in	Write D _{IN0} into semaphore flag
Х		Х	Н	Н	L	Data in	Data in	Write D _{IN0} into semaphore flag
L	Х	Х	L	Х	L			Not allowed
L	Х	Х	Х	L	L			Not allowed

Interrupt Operation Example

(Assumes $\overline{BUSY}_L = \overline{BUSY}_R = HIGH)^{[43]}$

			Left	Port	Right Port					
Function	R/W _L	CEL	OEL	A _{0L-14L}	INT _L	R/W _R	CER	OER	A _{0R-14R}	INT _R
Set right INT _R flag	L	L	Х	7FFF	Х	Х	Х	Х	Х	L ^[44]
Reset right INT _R flag	Х	Х	Х	X	Х	Х	L	L	7FFF	H ^[45]
Set left INT _L flag	Х	Х	Х	X	L ^[45]	L	L	Х	7FFE	Х
Reset left INT _L flag	Х	L	L	7FFE	H ^[44]	Х	Х	Х	Х	Х

 $43.\,A_{0l=15l}$ and $A_{0R=15R}$ FFFF/FFFE for the CY7C028V/038V. 44. If $\frac{BUSY_{l}}{BUSY_{R}}$ =L, then no change. 45. If $\frac{BUSY_{R}}{BUSY_{R}}$ =L, then no change.



Semaphore Operation Example

Function	I/O ₀ -I/O ₁₇ Left	I/O ₀ –I/O ₁₇ Right	Status
No action	1	1	Semaphore free
Left port writes 0 to semaphore	0	1	Left port has semaphore token
Right port writes 0 to semaphore	0	1	No change. Right side has no write access to semaphore
Left port writes 1 to semaphore	1	0	Right port obtains semaphore token
Left port writes 0 to semaphore	1	0	No change. Left port has no write access to semaphore
Right port writes 1 to semaphore	0	1	Left port obtains semaphore token
Left port writes 1 to semaphore	1	1	Semaphore free
Right port writes 0 to semaphore	1	0	Right port has semaphore token
Right port writes 1 to semaphore	1	1	Semaphore free
Left port writes 0 to semaphore	0	1	Left port has semaphore token
Left port writes 1 to semaphore	1	1	Semaphore free

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Ordering Information

32 K × 16 3.3 V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C027V-15AXC	A100	100-pin TQFP (Pb-free)	Commercial
	CY7C027V-15AXI	A100	100-pin TQFP (Pb-free)	Industrial
20	CY7C027V-20AC	A100	100-pin TQFP	Commercial
	CY7C027V-20AXC	A100	100-pin TQFP (Pb-free)	Commercial
25	CY7C027V-25AC	A100	100-pin TQFP	Commercial
	CY7C027V-25AXC	A100	100-pin TQFP (Pb-free)	Commercial
	CY7C027AV-25AXI	A100	100-pin TQFP (Pb-free)	Industrial

64 K × 16 3.3 V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C028V-15AXC	A100	100-pin TQFP (Pb-free)	Commercial
	CY7C028V-15AXI	A100	100-pin TQFP (Pb-free)	Industrial
20	CY7C028V-20AXC	A100	100-pin TQFP (Pb-free)	Commercial
	CY7C028V-20AI	A100	100-pin TQFP	Industrial
	CY7C028V-20AXI	A100	100-pin TQFP (Pb-free)	Industrial
25	CY7C028V-25AC	A100	100-pin TQFP	Commercial
	CY7C028V-25AXC	A100	100-pin TQFP (Pb-free)	Commercial
	CY7C028AV-25AXC	A100	100-pin TQFP (Pb-free)	Commercial

32 K × 18 3.3 V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
20	CY7C037AV-20AXC	A100	100-pin TQFP (Pb-free)	Commercial
	CY7C037AV-20AXI	A100	100-pin TQFP (Pb-free)	Industrial

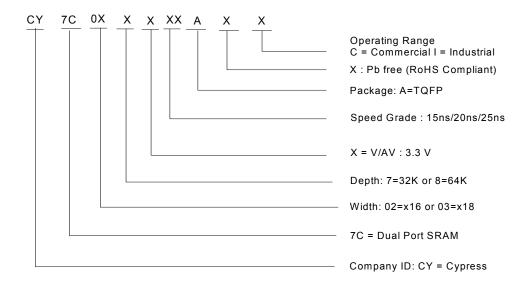
64 K × 18 3.3 V Asynchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
20	CY7C038V-20AXI	A100	100-pin TQFP (Pb-free)	Industrial

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Ordering Code Definitions

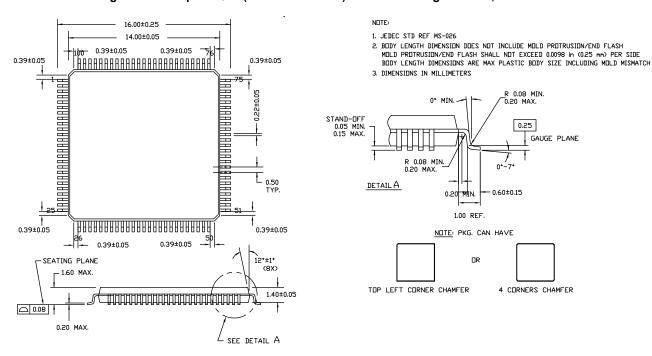


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Package Diagram

Figure 16. 100-pin TQFP (14 × 14 × 1.4 mm) A100SA Package Outline, 51-85048



51-85048 *H

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Acronyms

Acronym	Description		
CMOS	Complementary Metal Oxide Semiconductor		
I/O	Input/Output		
SRAM	Static Random Access Memory		
TQFP	Thin Quad Flat Pack		

Document Conventions

Units of Measure

Symbol	Unit of Measure		
°C	degree Celsius		
MHz	megahertz		
μΑ	microampere		
mA	milliampere		
mV	millivolt		
ns	nanosecond		
Ω	ohm		
pF	picofarad		
V	volt		
W	watt		

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Document History Page

Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
**	237626	YDT	6/30/04	Converted data sheet from old spec 38-00670 to conform with new data sheet. Removed cross information from features section
*A	259110	JHX	See ECN	Added Pb-Free packaging information.
*B	2623540	VKN / PYRS	12/17/08	Added CY7C027VN, CY7C027AV and CY7C037AV parts Updated Ordering information table
*C	2897217	RAME	03/22/2010	Updated Ordering Information Updated Package Diagram
*D	3093542	ADMU	11/25/2010	Removed information on CY7C027VN and CY7C037V Updated as per new template Added Acronyms and Units of Measure table Added Ordering Code Definitions Updated all footnotes
*E	3403652	ADMU	10/14/2011	removed pruned parts CY7C027V-25AI, CY7C038V-20AI from Ordering Information Updated Package Diagram.
*F	3845411	ADMU	01/29/2013	Updated Ordering Information (Updated part numbers). Updated Package Diagram: spec 51-85048 – Changed revision from *E to *G.
*G	3896090	ADMU	02/05/2013	Updated Ordering Information (Updated part numbers).
*H 4103305 ADM	ADMU	08/23/2013	Updated Features: Included CY7C028AV related information. Updated Pin Configurations: Included CY7C028AV related information.	
				Updated Architecture: Included CY7C028AV related information.
				Updated Functional Description: Included CY7C028AV related information.
				Updated Electrical Characteristics: Included CY7C028AV related information.
				Updated Data Retention Mode: Included CY7C028AV related information.
				Updated Switching Characteristics: Included CY7C028AV related information.
				Updated Switching Waveforms: Included CY7C028AV related information.
				Updated Ordering Information (Updated part numbers).
			Updated Package Diagram: spec 51-85048– Changed revision from *G to *H.	
				Updated in new template.

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